BUB323Z

NPN Silicon Power Darlington

High Voltage Autoprotected D^2PAK for Surface Mount

The BUB323Z is a planar, monolithic, high−voltage power Darlington with a built−in active zener clamping circuit. This device is specifically designed for unclamped, inductive applications such as Electronic Ignition, Switching Regulators and Motor Control.

Features

- Integrated High−Voltage Active Clamp
- Tight Clamping Voltage Window (350 V to 450 V) Guaranteed Over the −40°C to +125°C Temperature Range
- Clamping Energy Capability 100% Tested in a Live Ignition Circuit
- High DC Current Gain/Low Saturation Voltages Specified Over Full Temperature Range
- Design Guarantees Operation in SOA at All Times
- Pb−Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Sustaining Voltage	V_{CEO}	350	Vdc
Collector−Emitter Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous − Peak	I_C I_{CM}	10 20	Adc
Base Current − Continuous − Peak	I_B I_{BM}	3.0 6.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	150 1.0	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

THERMAL CHARACTERISTICS

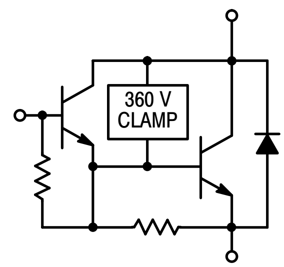
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	1.0	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8 in from Case for 5 Seconds	T_L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

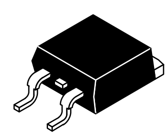
ON Semiconductor®

http://onsemi.com

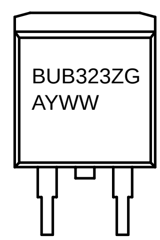
AUTOPROTECTED DARLINGTON
10 AMPERES
360−450 VOLTS CLAMP
150 WATTS



MARKING DIAGRAM



D^2PAK
CASE 418B
STYLE 1



BUB323Z = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (Note 1)					
Collector−Emitter Clamping Voltage (I_C = 7.0 A) (T_C = −40°C to +125°C)	V_{CLAMP}	350	−	450	Vdc
Collector−Emitter Cutoff Current (V_{CE} = 200 V, I_B = 0)	I_{CEO}	−	−	100	μAdc
Emitter−Base Leakage Current (V_{EB} = 6.0 Vdc, I_C = 0)	I_{EBO}	−	−	50	mAdc
ON CHARACTERISTICS (Note 1)					
Base−Emitter Saturation Voltage (I_C = 8.0 Adc, I_B = 100 mAdc) (I_C = 10 Adc, I_B = 0.25 Adc)	$V_{BE(sat)}$	 − −	 − −	 2.2 2.5	Vdc
Collector−Emitter Saturation Voltage (I_C = 7.0 Adc, I_B = 70 mAdc) (T_C = 125°C) (I_C = 8.0 Adc, I_B = 0.1 Adc) (T_C = 125°C) (I_C = 10 Adc, I_B = 0.25 Adc)	$V_{CE(sat)}$	 − − − − −	 − − − − −	 1.6 1.8 1.8 2.1 1.7	Vdc
Base−Emitter On Voltage (I_C = 5.0 Adc, V_{CE} = 2.0 Vdc) (T_C = −40°C to +125°C) (I_C = 8.0 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	 1.1 1.3	 − −	 2.1 2.3	Vdc
Diode Forward Voltage Drop (I_F = 10 Adc)	V_F	−	−	2.5	Vdc
DC Current Gain (I_C = 6.5 Adc, V_{CE} = 1.5 Vdc) (T_C = −40°C to +125°C) (I_C = 5.0 Adc, V_{CE} = 4.6 Vdc)	h_{FE}	 150 500	 − −	 − 3400	−
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth (I_C = 0.2 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	−	−	2.0	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	−	−	200	pF
Input Capacitance (V_{EB} = 6.0 V)	C_{ib}	−	−	550	pF
CLAMPING ENERGY (See Notes)					
Repetitive Non−Destructive Energy Dissipated at turn−off: (I_C = 7.0 A, L = 8.0 mH, R_{BE} = 100 Ω) (see Figures 2 and 4)	W_{CLAMP}	200	−	−	mJ
SWITCHING CHARACTERISTICS: Inductive Load (L = 10 mH)					
Fall Time (I_C = 6.5 A, I_{B1} = 45 mA, $V_{BE(off)}$ = 0, $R_{BE(off)}$ = 0, V_{CC} = 14 V, V_Z = 300 V)	t_{fi}	−	625	−	ns
Storage Time	t_{si}	−	10	30	μs
Cross−over Time	t_c	−	1.7	−	μs

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

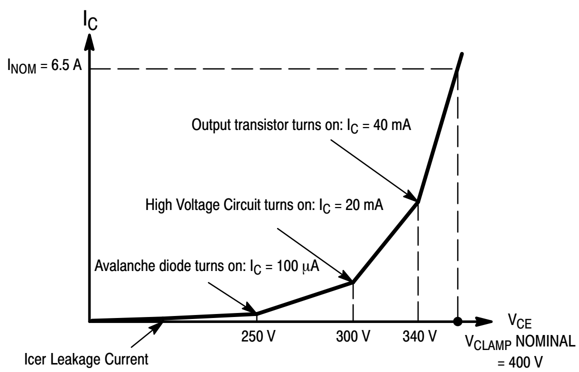


Figure 1. $I_C = f(V_{CE})$ Curve Shape

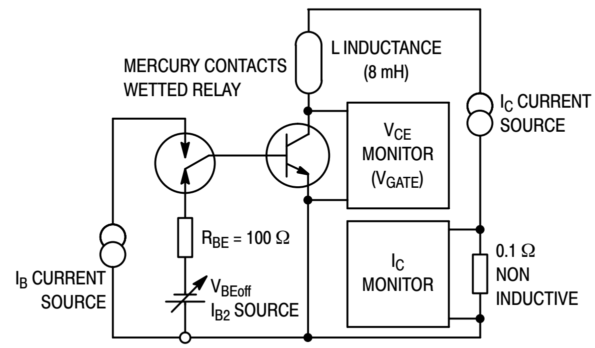


Figure 2. Basic Energy Test Circuit

By design, the BU323Z has a built−in avalanche diode and a special high voltage driving circuit. During an auto−protect cycle, the transistor is turned on again as soon as a voltage, determined by the zener threshold and the network, is reached. This prevents the transistor from going into a Reverse Bias Operating limit condition. Therefore, the device will have an extended safe operating area and will always appear to be in "FBSOA." Because of the built−in zener and associated network, the $I_C = f(V_{CE})$ curve exhibits an unfamiliar shape compared to standard products as shown in Figure 1.

The bias parameters, V_{CLAMP}, I_{B1}, $V_{BE(off)}$, I_{B2}, I_C, and the inductance, are applied according to the Device Under Test (DUT) specifications. V_{CE} and I_C are monitored by the test system while making sure the load line remains within the limits as described in Figure 4.

Note: All BU323Z ignition devices are 100% energy tested, per the test circuit and criteria described in Figures 2 and 4, to the minimum guaranteed repetitive energy, as specified in the device parameter section. The device can sustain this energy on a repetitive basis without degrading any of the specified electrical characteristics of the devices. The units under test are kept functional during the complete test sequence for the test conditions described:
$I_{C(peak)}$ = 7.0 A, I_CH = 5.0 A, I_CL = 100 mA, I_B = 100 mA, R_{BE} = 100 Ω, V_{gate} = 280 V, L = 8.0 mH

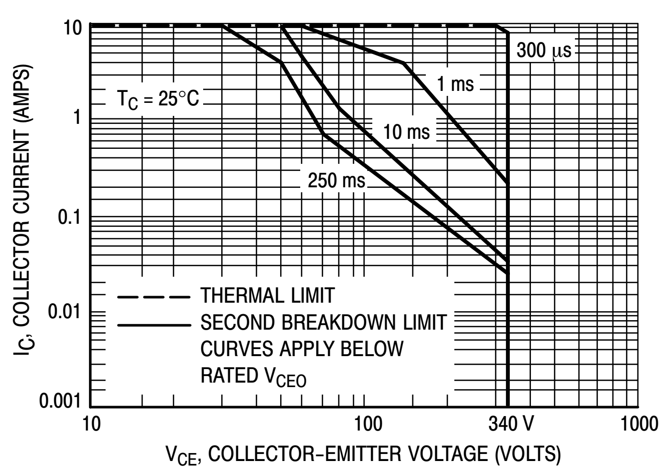
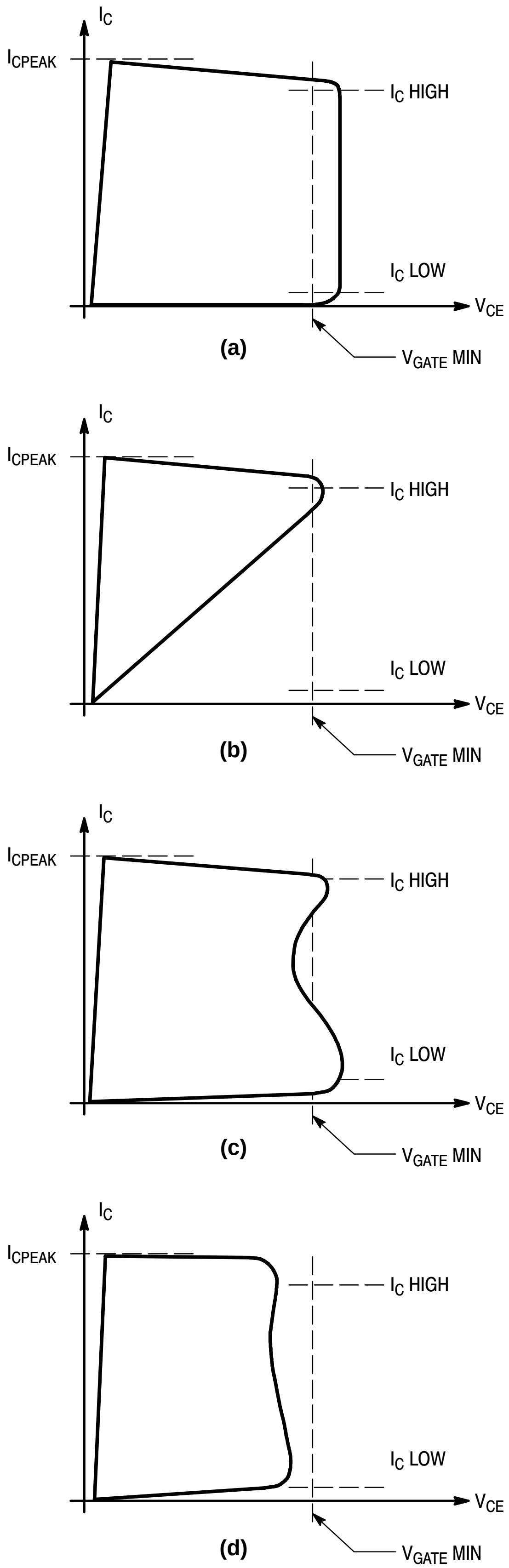


Figure 3. Forward Bias Safe Operating Area



The shaded area represents the amount of energy the device can sustain, under given DC biases (I_C/I_B/$V_{BE(off)}$/R_{BE}), without an external clamp; see the test schematic diagram, Figure 2.

The transistor PASSES the Energy test if, for the inductive load and I_{CPEAK}/I_B/$V_{BE(off)}$ biases, the V_{CE} remains outside the shaded area and greater than the V_{GATE} minimum limit, Figure 4a.

The transistor FAILS if the V_{CE} is less than the V_{GATE} (minimum limit) at any point along the V_{CE}/I_C curve as shown on Figures 4b, and 4c. This assures that hot spots and uncontrolled avalanche are not being generated in the die, and the transistor is not damaged, thus enabling the sustained energy level required.

The transistor FAILS if its Collector/Emitter breakdown voltage is less than the V_{GATE} value, Figure 4d.

Figure 4. Energy Test Criteria for BU323Z

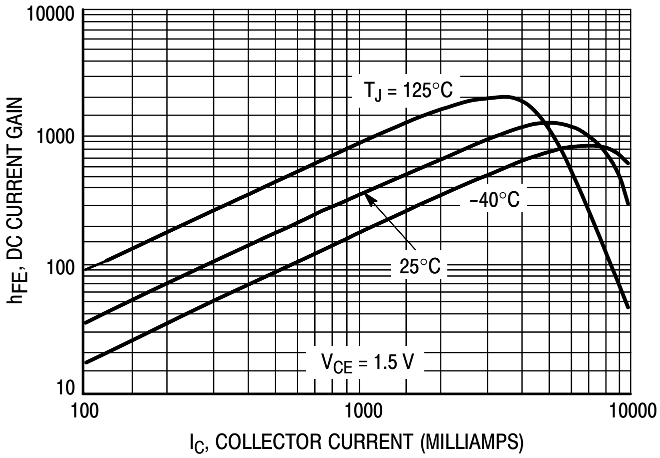


Figure 5. DC Current Gain

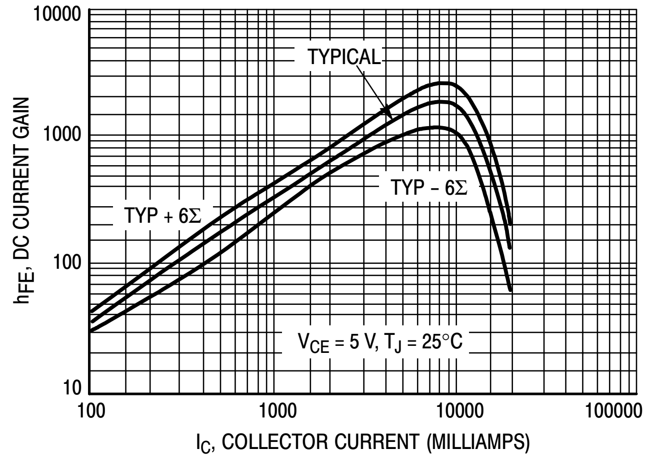


Figure 6. DC Current Gain

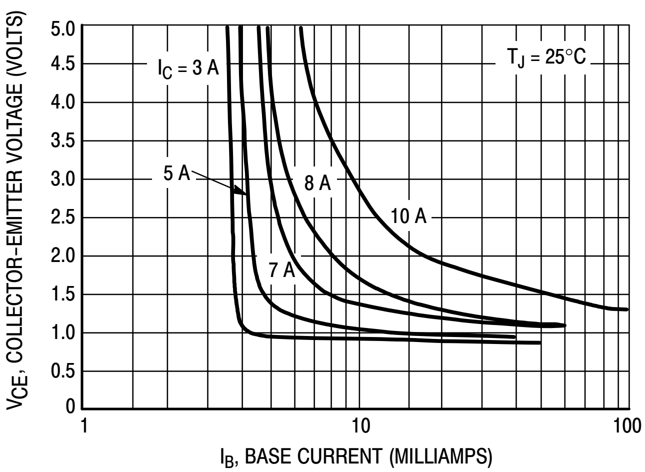


Figure 7. Collector Saturation Region

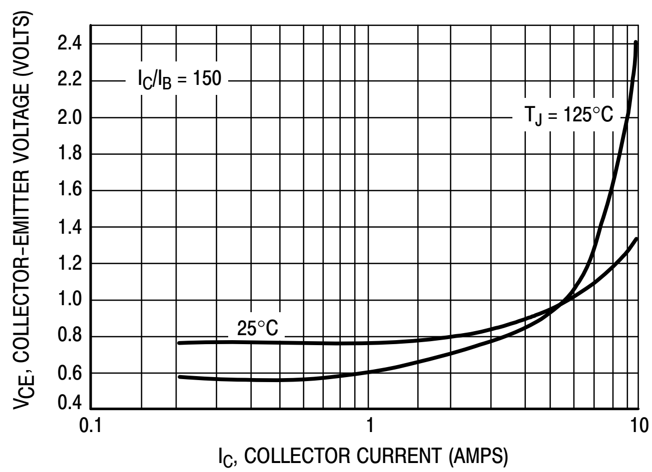


Figure 8. Collector−Emitter Saturation Voltage

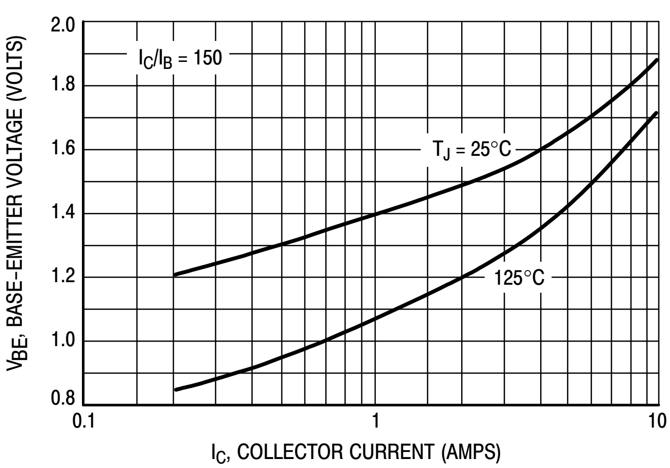


Figure 9. Base−Emitter Saturation Voltage

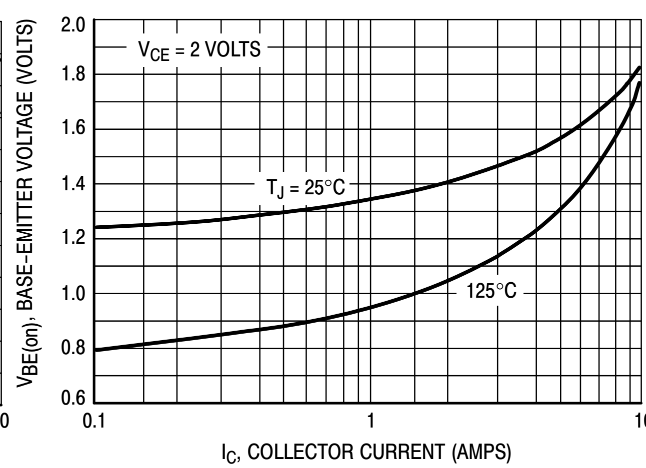


Figure 10. Base−Emitter “ON” Voltages

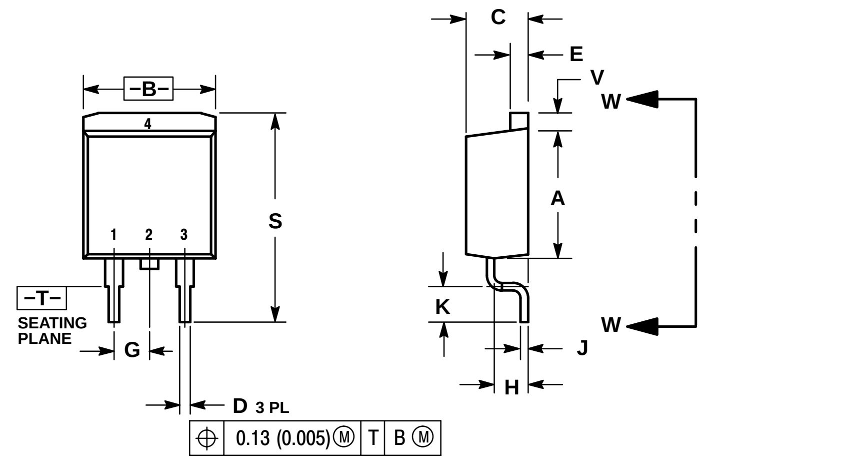
ORDERING INFORMATION

Device	Package	Shipping†
BUB323Z	D^2PAK	50 Units / Rail
BUB323ZG	D^2PAK (Pb−Free)	50 Units / Rail
BUB323ZT4	D^2PAK	800 Units / Tape & Reel
BUB323ZT4G	D^2PAK (Pb−Free)	800 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

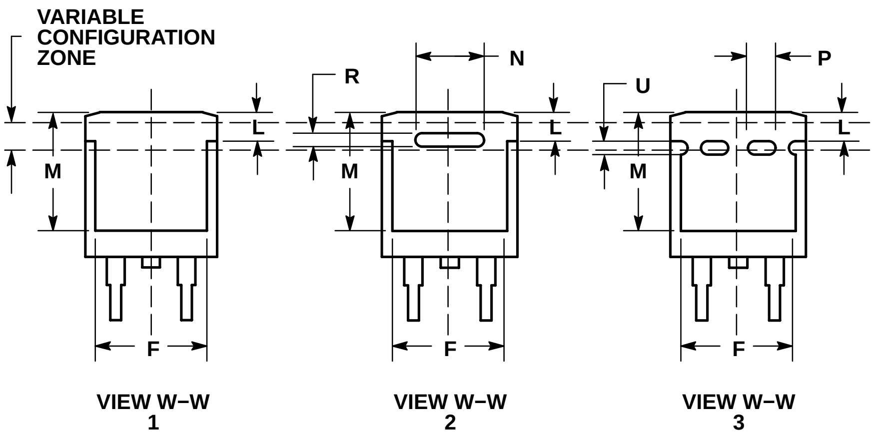
D^{2}PAK
CASE 418B−04
ISSUE J



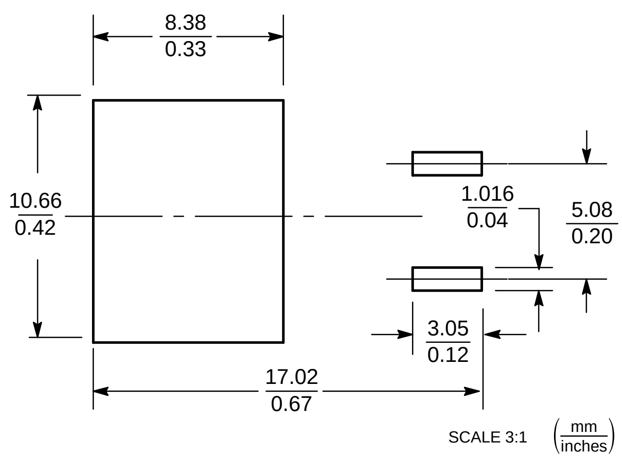
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B−01 THRU 418B−03 OBSOLETE, NEW STANDARD 418B−04.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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